

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±10	V		
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$	ΙD	6.2	Α
Maximum Body Diode Forward Current (Note 6)			Is	2	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	1.15	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	D	107	°C/W
	t<10s	$R_{\theta JA}$	76	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	1.75	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state		75	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	50	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	16	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

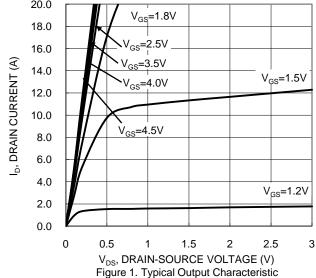
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

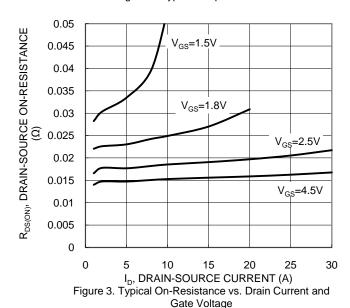
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				•			
Drain-Source Breakdown Voltage	BV_{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			18	24	mΩ	$V_{GS} = 4.5V, I_D = 6.2A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	21	32		V _{GS} = 2.5V, I _D = 5.2A	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	887	_		V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	91	_	pF		
Reverse Transfer Capacitance	C_{rss}	_	37	_			
Gate Resistance	R_g	_	191	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	10	_			
Total Gate Charge (V _{GS} = 8V)	Q_g	_	18.4	_	nC	$V_{DS} = 10V, I_{D} = 6.5A$	
Gate-Source Charge	Q_{gs}	_	1.3	_	no.		
Gate-Drain Charge	Q_{gd}	_	1.8	_			
Turn-On Delay Time	t _{D(ON)}	_	53	_		$V_{DS} = 10V, V_{GS} = 4.5V,$ $R_G = 6\Omega, R_L = 10\Omega, I_D = 1A$	
Turn-On Rise Time	t _R	_	66	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	619	_	118		
Turn-Off Fall Time	t _F	_	197	_			
Reverse Recovery Time	t _{RR}	_	119	_	ns	I _F = 4A, di/dt = 100A/μs	
Reverse Recovery Charge	Q_{RR}		96	_	nC	I _F = 4A, di/dt = 100A/μs	

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

20.0





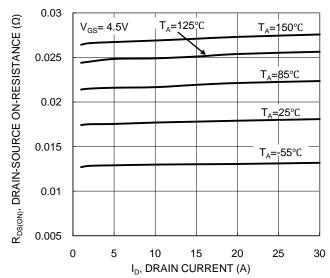
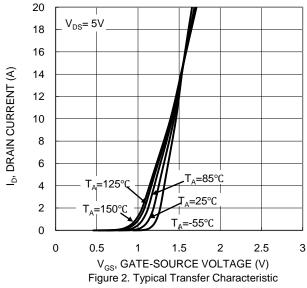
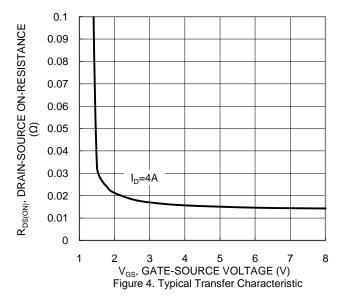


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



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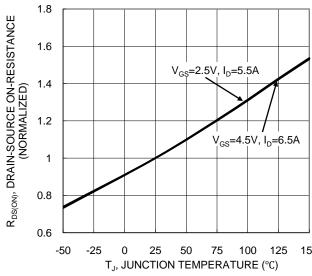
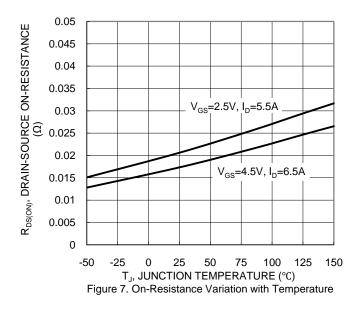
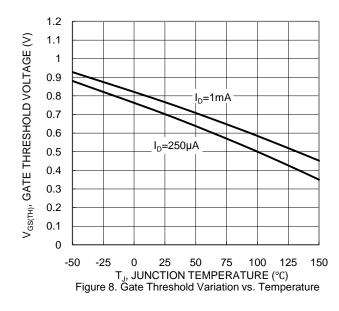
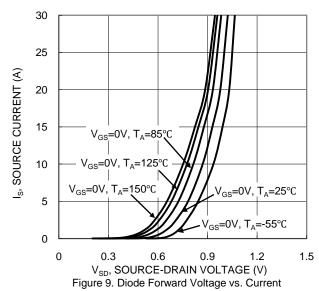


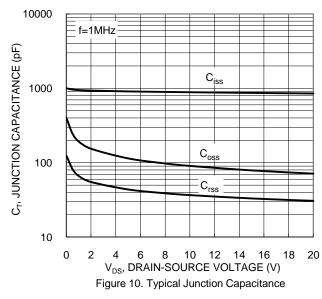
Figure 6. On-Resistance Variation with Temperature

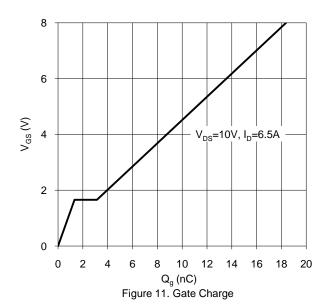


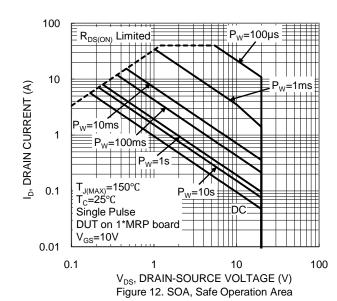




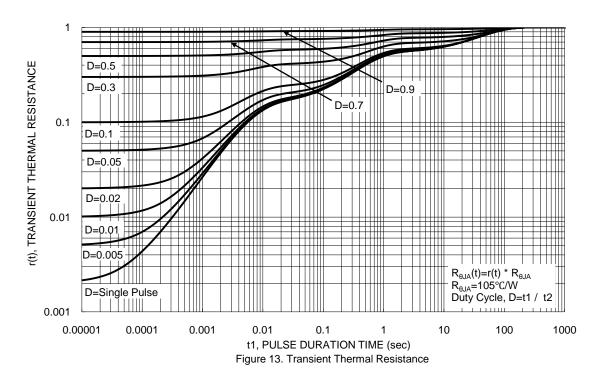






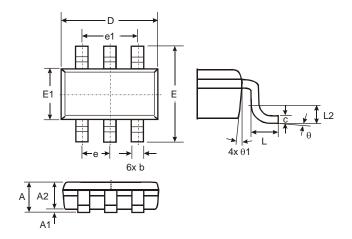






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

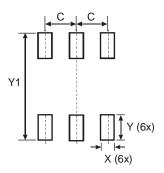


TSOT26					
Dim	Min	Max	Тур		
Α	-	1.00			
A1	0.01	0.10			
A2	0.84	0.90			
D			2.90		
Е			2.80		
E1	_	_	1.60		
b	0.30	0.45			
С	0.12	0.20	_		
е	_	_	0.95		
e1			1.90		
L	0.30	0.50			
L2	-	-	0.25		
θ	0°	8°	4°		
θ1	4°	12°	_		
All D	All Dimensions in mm				



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199

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